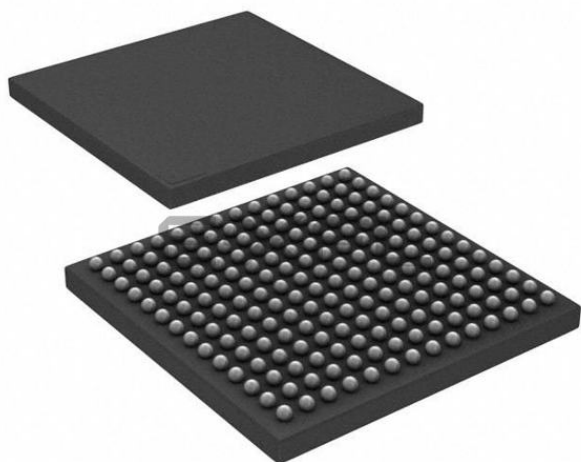




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Understanding [Embedded - FPGAs \(Field Programmable Gate Array\)](#)

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications.

Details

Product Status	Active
Number of LABs/CLBs	-
Number of Logic Elements/Cells	6000
Total RAM Bits	184320
Number of I/O	100
Number of Gates	-
Voltage - Supply	0.95V ~ 1.05V
Mounting Type	Surface Mount
Operating Temperature	0°C ~ 85°C (TJ)
Package / Case	196-LBGA, CSPBGA
Supplier Device Package	196-CSBGA (15x15)
Purchase URL	https://www.e-xfl.com/product-detail/xilinx/xc7s6-1ftgb196c

Table 3: DC Characteristics Over Recommended Operating Conditions

Symbol	Description	Min	Typ ⁽¹⁾	Max	Units
V_{DRINT}	Data retention V_{CCINT} voltage (below which configuration data might be lost).	0.75	–	–	V
V_{DRI}	Data retention V_{CCAUX} voltage (below which configuration data might be lost).	1.5	–	–	V
I_{REF}	V_{REF} leakage current per pin.	–	–	15	μA
I_{L}	Input or output leakage current per pin (sample-tested).	–	–	15	μA
$C_{\text{IN}}^{(2)}$	Die input capacitance at the pad.	–	–	8	pF
I_{RPU}	Pad pull-up (when selected) at $V_{\text{IN}} = 0\text{V}$, $V_{\text{CCO}} = 3.3\text{V}$.	90	–	330	μA
	Pad pull-up (when selected) at $V_{\text{IN}} = 0\text{V}$, $V_{\text{CCO}} = 2.5\text{V}$.	68	–	250	μA
	Pad pull-up (when selected) at $V_{\text{IN}} = 0\text{V}$, $V_{\text{CCO}} = 1.8\text{V}$.	34	–	220	μA
	Pad pull-up (when selected) at $V_{\text{IN}} = 0\text{V}$, $V_{\text{CCO}} = 1.5\text{V}$.	23	–	150	μA
	Pad pull-up (when selected) at $V_{\text{IN}} = 0\text{V}$, $V_{\text{CCO}} = 1.2\text{V}$.	12	–	120	μA
I_{RPD}	Pad pull-down (when selected) at $V_{\text{IN}} = 3.3\text{V}$.	68	–	330	μA
I_{CCADC}	Analog supply current, analog circuits in powered up state.	–	–	25	mA
$I_{\text{BATT}}^{(3)}$	Battery supply current.	–	–	150	nA
$R_{\text{IN_TERM}}^{(4)}$	Thevenin equivalent resistance of programmable input termination to $V_{\text{CCO}}/2$ (UNTUNED_SPLIT_40).	28	40	55	Ω
	Thevenin equivalent resistance of programmable input termination to $V_{\text{CCO}}/2$ (UNTUNED_SPLIT_50).	35	50	65	Ω
	Thevenin equivalent resistance of programmable input termination to $V_{\text{CCO}}/2$ (UNTUNED_SPLIT_60).	44	60	83	Ω
n	Temperature diode ideality factor.	–	1.010	–	–
r	Temperature diode series resistance.	–	2	–	Ω

Notes:

1. Typical values are specified at nominal voltage, 25°C.
2. This measurement represents the die capacitance at the pad, not including the package.
3. Maximum value specified for worst case process at 25°C.
4. Termination resistance to a $V_{\text{CCO}}/2$ level.

Table 5: Typical Quiescent Supply Current⁽¹⁾⁽²⁾⁽³⁾ (Cont'd)

Symbol	Description	Device	Speed Grade						Units
			1.0V					0.95V	
			-2C	-2I	-1C	-1I	-1Q	-1LI	
I_{CCOQ}	Quiescent V_{CCO} supply current.	XC7S6	1	1	1	1	1	1	mA
		XC7S15	1	1	1	1	1	1	mA
		XC7S25	1	1	1	1	1	1	mA
		XC7S50	1	1	1	1	1	1	mA
		XC7S75	4	4	4	4	4	4	mA
		XC7S100	4	4	4	4	4	4	mA
		XA7S6	N/A	1	N/A	1	1	N/A	mA
		XA7S15	N/A	1	N/A	1	1	N/A	mA
		XA7S25	N/A	1	N/A	1	1	N/A	mA
		XA7S50	N/A	1	N/A	1	1	N/A	mA
		XA7S75	N/A	4	N/A	4	4	N/A	mA
		XA7S100	N/A	4	N/A	4	4	N/A	mA
I_{CCAUXQ}	Quiescent V_{CCAUX} supply current.	XC7S6	10	10	10	10	10	10	mA
		XC7S15	10	10	10	10	10	10	mA
		XC7S25	13	13	13	13	13	13	mA
		XC7S50	22	22	22	22	22	20	mA
		XC7S75	43	43	43	43	43	43	mA
		XC7S100	43	43	43	43	43	43	mA
		XA7S6	N/A	10	N/A	10	10	N/A	mA
		XA7S15	N/A	10	N/A	10	10	N/A	mA
		XA7S25	N/A	13	N/A	13	13	N/A	mA
		XA7S50	N/A	22	N/A	22	22	N/A	mA
		XA7S75	N/A	43	N/A	43	43	N/A	mA
		XA7S100	N/A	43	N/A	43	43	N/A	mA

Table 6 shows the minimum current, in addition to I_{CCQ} maximum, that is required by Spartan-7 devices for proper power-on and configuration. If the current minimums shown in Table 6 are met, the device powers on after all four supplies have passed through their power-on reset threshold voltages. The FPGA must not be configured until after V_{CCINT} is applied. Once initialized and configured, use the *Xilinx Power Estimator* spreadsheet tool [Ref 6] to estimate current drain on these supplies.

Table 6: Power-On Current

Device	$I_{CCINTMIN}$	$I_{CCAUXMIN}$	I_{CCOMIN}	$I_{CCBRAMMIN}$	Units
XC7S6	$I_{CCINTQ} + 120$	$I_{CCAUXQ} + 40$	$I_{CCOQ} + 40$ mA per bank	$I_{CCBRAMQ} + 60$	mA
XC7S15	$I_{CCINTQ} + 120$	$I_{CCAUXQ} + 40$	$I_{CCOQ} + 40$ mA per bank	$I_{CCBRAMQ} + 60$	mA
XC7S25	$I_{CCINTQ} + 120$	$I_{CCAUXQ} + 40$	$I_{CCOQ} + 40$ mA per bank	$I_{CCBRAMQ} + 60$	mA
XC7S50	$I_{CCINTQ} + 120$	$I_{CCAUXQ} + 40$	$I_{CCOQ} + 40$ mA per bank	$I_{CCBRAMQ} + 60$	mA
XC7S75	$I_{CCINTQ} + 300$	$I_{CCAUXQ} + 140$	$I_{CCOQ} + 40$ mA per bank	$I_{CCBRAMQ} + 60$	mA
XC7S100	$I_{CCINTQ} + 300$	$I_{CCAUXQ} + 140$	$I_{CCOQ} + 40$ mA per bank	$I_{CCBRAMQ} + 60$	mA
XA7S6	$I_{CCINTQ} + 120$	$I_{CCAUXQ} + 40$	$I_{CCOQ} + 40$ mA per bank	$I_{CCBRAMQ} + 60$	mA
XA7S15	$I_{CCINTQ} + 120$	$I_{CCAUXQ} + 40$	$I_{CCOQ} + 40$ mA per bank	$I_{CCBRAMQ} + 60$	mA
XA7S25	$I_{CCINTQ} + 120$	$I_{CCAUXQ} + 40$	$I_{CCOQ} + 40$ mA per bank	$I_{CCBRAMQ} + 60$	mA
XA7S50	$I_{CCINTQ} + 120$	$I_{CCAUXQ} + 40$	$I_{CCOQ} + 40$ mA per bank	$I_{CCBRAMQ} + 60$	mA
XA7S75	$I_{CCINTQ} + 300$	$I_{CCAUXQ} + 140$	$I_{CCOQ} + 40$ mA per bank	$I_{CCBRAMQ} + 60$	mA
XA7S100	$I_{CCINTQ} + 300$	$I_{CCAUXQ} + 140$	$I_{CCOQ} + 40$ mA per bank	$I_{CCBRAMQ} + 60$	mA

Table 7: Power Supply Ramp Time

Symbol	Description	Conditions	Min	Max	Units
T_{VCCINT}	Ramp time from GND to 90% of V_{CCINT} .		0.2	50	ms
T_{VCCO}	Ramp time from GND to 90% of V_{CCO} .		0.2	50	ms
T_{VCCAUX}	Ramp time from GND to 90% of V_{CCAUX} .		0.2	50	ms
$T_{VCCBRAM}$	Ramp time from GND to 90% of V_{CCBRAM} .		0.2	50	ms
$T_{VCCO2VCCAUX}$	Allowed time per power cycle for $V_{CCO} - V_{CCAUX} > 2.625V$.	$T_J = 125^{\circ}C^{(1)}$	–	300	ms
		$T_J = 100^{\circ}C^{(1)}$	–	500	ms
		$T_J = 85^{\circ}C^{(1)}$	–	800	ms

Notes:

- Based on 240,000 power cycles with a nominal V_{CCO} of 3.3V or 36,500 power cycles with a worst case V_{CCO} of 3.465V.

Table 9: Differential SelectIO DC Input and Output Levels

I/O Standard	$V_{ICM}^{(1)}$			$V_{ID}^{(2)}$			$V_{OCM}^{(3)}$			$V_{OD}^{(4)}$		
	V, Min	V, Typ	V, Max	V, Min	V, Typ	V, Max	V, Min	V, Typ	V, Max	V, Min	V, Typ	V, Max
BLVDS_25	0.300	1.200	1.425	0.100	—	—	—	1.250	—	Note 5		
MINI_LVDS_25	0.300	1.200	V_{CCAUX}	0.200	0.400	0.600	1.000	1.200	1.400	0.300	0.450	0.600
PPDS_25	0.200	0.900	V_{CCAUX}	0.100	0.250	0.400	0.500	0.950	1.400	0.100	0.250	0.400
RSDS_25	0.300	0.900	1.500	0.100	0.350	0.600	1.000	1.200	1.400	0.100	0.350	0.600
TMDS_33	2.700	2.965	3.230	0.150	0.675	1.200	$V_{CCO} - 0.405$	$V_{CCO} - 0.300$	$V_{CCO} - 0.190$	0.400	0.600	0.800

Notes:

- V_{ICM} is the input common mode voltage.
- V_{ID} is the input differential voltage ($Q - \overline{Q}$).
- V_{OCM} is the output common mode voltage.
- V_{OD} is the output differential voltage ($Q - \overline{Q}$).
- V_{OD} for BLVDS will vary significantly depending on topology and loading.

Table 10: Complementary Differential SelectIO DC Input and Output Levels

I/O Standard	$V_{ICM}^{(1)}$			$V_{ID}^{(2)}$		$V_{OL}^{(3)}$	$V_{OH}^{(4)}$	I_{OL}	I_{OH}
	V, Min	V, Typ	V, Max	V, Min	V, Max	V, Max	V, Min	mA, Max	mA, Min
DIFF_HSTL_I	0.300	0.750	1.125	0.100	—	0.400	$V_{CCO} - 0.400$	8.00	–8.00
DIFF_HSTL_I_18	0.300	0.900	1.425	0.100	—	0.400	$V_{CCO} - 0.400$	8.00	–8.00
DIFF_HSTL_II	0.300	0.750	1.125	0.100	—	0.400	$V_{CCO} - 0.400$	16.00	–16.00
DIFF_HSTL_II_18	0.300	0.900	1.425	0.100	—	0.400	$V_{CCO} - 0.400$	16.00	–16.00
DIFF_HSUL_12	0.300	0.600	0.850	0.100	—	20% V_{CCO}	80% V_{CCO}	0.100	–0.100
DIFF_MOBILE_DDR	0.300	0.900	1.425	0.100	—	10% V_{CCO}	90% V_{CCO}	0.100	–0.100
DIFF_SSTL135	0.300	0.675	1.000	0.100	—	$(V_{CCO}/2) - 0.150$	$(V_{CCO}/2) + 0.150$	13.0	–13.0
DIFF_SSTL135_R	0.300	0.675	1.000	0.100	—	$(V_{CCO}/2) - 0.150$	$(V_{CCO}/2) + 0.150$	8.9	–8.9
DIFF_SSTL15	0.300	0.750	1.125	0.100	—	$(V_{CCO}/2) - 0.175$	$(V_{CCO}/2) + 0.175$	13.0	–13.0
DIFF_SSTL15_R	0.300	0.750	1.125	0.100	—	$(V_{CCO}/2) - 0.175$	$(V_{CCO}/2) + 0.175$	8.9	–8.9
DIFF_SSTL18_I	0.300	0.900	1.425	0.100	—	$(V_{CCO}/2) - 0.470$	$(V_{CCO}/2) + 0.470$	8.00	–8.00
DIFF_SSTL18_II	0.300	0.900	1.425	0.100	—	$(V_{CCO}/2) - 0.600$	$(V_{CCO}/2) + 0.600$	13.4	–13.4

Notes:

- V_{ICM} is the input common mode voltage.
- V_{ID} is the input differential voltage ($Q - \overline{Q}$).
- V_{OL} is the single-ended low-output voltage.
- V_{OH} is the single-ended high-output voltage.

Table 15: Networking Applications Interface Performances (Cont'd)

Description	V _{CCINT} Operating Voltage, Speed Grade, and Temperature Range			Units
	1.0V		0.95V	
	-2C/-2I	-1C/-1I/-1Q	-1LI	
DDR LVDS receiver ⁽¹⁾	1250	950	950	Mb/s

Notes:

1. LVDS receivers are typically bounded with certain applications where specific dynamic phase-alignment (DPA) algorithms dominate deterministic performance.

Table 16: Maximum Physical Interface (PHY) Rate for Memory Interface IP available with the Memory Interface Generator⁽¹⁾

Memory Standard	V _{CCINT} Operating Voltage, Speed Grade, and Temperature Range			Units
	1.0V		0.95V	
	-2C/-2I	-1C/-1I/-1Q	-1LI	
4:1 Memory Controllers				
DDR3	800 ⁽²⁾	667	667	Mb/s
DDR3L	800 ⁽²⁾	667	667	Mb/s
DDR2	800 ⁽²⁾	667	667	Mb/s
2:1 Memory Controllers				
DDR3	800 ⁽²⁾	667	667	Mb/s
DDR3L	800 ⁽²⁾	667	667	Mb/s
DDR2	800 ⁽²⁾	667	667	Mb/s
LPDDR2	667	533	533	Mb/s

Notes:

1. V_{REF} tracking is required. For more information, see the *Zynq-7000 AP SoC and 7 Series FPGAs Memory Interface Solutions User Guide* (UG586) [Ref 7].
2. The maximum PHY rate is 667 Mb/s in the FTGB196 package.

IOB Pad Input/Output/3-State

Table 17 summarizes the values of standard-specific data input delay adjustments, output delays terminating at pads (based on standard) and 3-state delays.

- T_{IOPi} is described as the delay from IOB pad through the input buffer to the I-pin of an IOB pad. The delay varies depending on the capability of the SelectIO input buffer.
- T_{IOPo} is described as the delay from the O pin to the IOB pad through the output buffer of an IOB pad. The delay varies depending on the capability of the SelectIO output buffer.
- T_{IOTp} is described as the delay from the T pin to the IOB pad through the output buffer of an IOB pad, when 3-state is disabled. The delay varies depending on the SelectIO capability of the output buffer. In HR I/O banks, the IN_TERM termination turn-on time is always faster than T_{IOTp} when the INTERMDISABLE pin is used.

Table 17: IOB High Range (HR) Switching Characteristics (Cont'd)

I/O Standard	T _{IOPI}			T _{IOOP}			T _{IOTP}			Units
	V _{CCINT} Operating Voltage and Speed Grade									
	1.0V		0.95V	1.0V		0.95V	1.0V		0.95V	
	-2	-1	-1L	-2	-1	-1L	-2	-1	-1L	
HSTL_II_18_F	0.75	0.81	0.81	1.24	1.49	1.49	1.27	1.51	1.51	ns
DIFF_HSTL_I_F	0.76	0.83	0.83	1.30	1.56	1.56	1.33	1.57	1.57	ns
DIFF_HSTL_II_F	0.76	0.83	0.83	1.33	1.59	1.59	1.36	1.60	1.60	ns
DIFF_HSTL_I_18_F	0.79	0.86	0.86	1.33	1.59	1.59	1.36	1.60	1.60	ns
DIFF_HSTL_II_18_F	0.78	0.85	0.85	1.33	1.59	1.59	1.36	1.60	1.60	ns
LVC MOS33_S4	1.34	1.41	1.41	3.93	4.18	4.18	3.96	4.20	4.20	ns
LVC MOS33_S8	1.34	1.41	1.41	3.65	3.90	3.90	3.68	3.91	3.91	ns
LVC MOS33_S12	1.34	1.41	1.41	3.21	3.46	3.46	3.24	3.48	3.48	ns
LVC MOS33_S16	1.34	1.41	1.41	3.52	3.77	3.77	3.55	3.79	3.79	ns
LVC MOS33_F4	1.34	1.41	1.41	3.38	3.64	3.64	3.41	3.65	3.65	ns
LVC MOS33_F8	1.34	1.41	1.41	2.87	3.12	3.12	2.90	3.13	3.13	ns
LVC MOS33_F12	1.34	1.41	1.41	2.68	2.93	2.93	2.71	2.95	2.95	ns
LVC MOS33_F16	1.34	1.41	1.41	2.68	2.93	2.93	2.71	2.95	2.95	ns
LVC MOS25_S4	1.20	1.27	1.27	3.26	3.51	3.51	3.29	3.52	3.52	ns
LVC MOS25_S8	1.20	1.27	1.27	3.01	3.26	3.26	3.04	3.27	3.27	ns
LVC MOS25_S12	1.20	1.27	1.27	2.60	2.85	2.85	2.63	2.87	2.87	ns
LVC MOS25_S16	1.20	1.27	1.27	2.94	3.20	3.20	2.97	3.21	3.21	ns
LVC MOS25_F4	1.20	1.27	1.27	2.87	3.12	3.12	2.90	3.13	3.13	ns
LVC MOS25_F8	1.20	1.27	1.27	2.30	2.56	2.56	2.33	2.57	2.57	ns
LVC MOS25_F12	1.20	1.27	1.27	2.29	2.54	2.54	2.32	2.55	2.55	ns
LVC MOS25_F16	1.20	1.27	1.27	2.13	2.39	2.39	2.16	2.40	2.40	ns
LVC MOS18_S4	0.83	0.89	0.89	1.74	1.99	1.99	1.77	2.01	2.01	ns
LVC MOS18_S8	0.83	0.89	0.89	2.30	2.56	2.56	2.33	2.57	2.57	ns
LVC MOS18_S12	0.83	0.89	0.89	2.30	2.56	2.56	2.33	2.57	2.57	ns
LVC MOS18_S16	0.83	0.89	0.89	1.65	1.90	1.90	1.68	1.91	1.91	ns
LVC MOS18_S24	0.83	0.89	0.89	1.72	1.98	1.98	1.75	1.99	1.99	ns
LVC MOS18_F4	0.83	0.89	0.89	1.57	1.82	1.82	1.60	1.84	1.84	ns
LVC MOS18_F8	0.83	0.89	0.89	1.80	2.06	2.06	1.83	2.07	2.07	ns
LVC MOS18_F12	0.83	0.89	0.89	1.80	2.06	2.06	1.83	2.07	2.07	ns
LVC MOS18_F16	0.83	0.89	0.89	1.52	1.77	1.77	1.55	1.79	1.79	ns
LVC MOS18_F24	0.83	0.89	0.89	1.46	1.71	1.71	1.49	1.73	1.73	ns
LVC MOS15_S4	0.86	0.93	0.93	2.18	2.43	2.43	2.21	2.45	2.45	ns
LVC MOS15_S8	0.86	0.93	0.93	2.21	2.46	2.46	2.24	2.48	2.48	ns
LVC MOS15_S12	0.86	0.93	0.93	1.71	1.96	1.96	1.74	1.98	1.98	ns
LVC MOS15_S16	0.86	0.93	0.93	1.71	1.96	1.96	1.74	1.98	1.98	ns
LVC MOS15_F4	0.86	0.93	0.93	1.97	2.23	2.23	2.00	2.24	2.24	ns

Table 18: IOB 3-state Output Switching Characteristics

Symbol	Description	V _{CCINT} Operating Voltage and Speed Grade			Units
		1.0V		0.95V	
		-2	-1	-1L	
T _{IOTPHZ}	T input to pad high-impedance.	2.19	2.37	2.37	ns
T _{IOIBUFDISABLE}	IBUF turn-on time from IBUFDISABLE to O output.	2.30	2.60	2.60	ns

I/O Standard Adjustment Measurement Methodology

Input Delay Measurements

Table 19 shows the test setup parameters used for measuring input delay.

Table 19: Input Delay Measurement Methodology

Description	I/O Standard Attribute	$V_L^{(1)}$	$V_H^{(1)}$	$V_{MEAS}^{(3)(5)}$	$V_{REF}^{(2)(4)}$
LVCMOS, 1.2V	LVCMOS12	0.1	1.1	0.6	—
LVCMOS, 1.5V	LVCMOS15	0.1	1.4	0.75	—
LVCMOS, 1.8V	LVCMOS18	0.1	1.7	0.9	—
LVCMOS, 2.5V	LVCMOS25	0.1	2.4	1.25	—
LVCMOS, 3.3V	LVCMOS33	0.1	3.2	1.65	—
LVTTL, 3.3V	LVTTL	0.1	3.2	1.65	—
MOBILE_DDR, 1.8V	MOBILE_DDR	0.1	1.7	0.9	—
PCI33, 3.3V	PCI33_3	0.1	3.2	1.65	—
HSTL (high-speed transceiver logic), Class I, 1.2V	HSTL_I_12	$V_{REF} - 0.5$	$V_{REF} + 0.5$	V_{REF}	0.60
HSTL, Class I & II, 1.5V	HSTL_I, HSTL_II	$V_{REF} - 0.65$	$V_{REF} + 0.65$	V_{REF}	0.75
HSTL, Class I & II, 1.8V	HSTL_I_18, HSTL_II_18	$V_{REF} - 0.8$	$V_{REF} + 0.8$	V_{REF}	0.90
HSUL (high-speed unterminated logic), 1.2V	HSUL_12	$V_{REF} - 0.5$	$V_{REF} + 0.5$	V_{REF}	0.60
SSTL (stub-terminated transceiver logic), 1.2V	SSTL12	$V_{REF} - 0.5$	$V_{REF} + 0.5$	V_{REF}	0.60
SSTL, 1.35V	SSTL135, SSTL135_R	$V_{REF} - 0.575$	$V_{REF} + 0.575$	V_{REF}	0.675
SSTL, 1.5V	SSTL15, SSTL15_R	$V_{REF} - 0.65$	$V_{REF} + 0.65$	V_{REF}	0.75
SSTL, Class I & II, 1.8V	SSTL18_I, SSTL18_II	$V_{REF} - 0.8$	$V_{REF} + 0.8$	V_{REF}	0.90
DIFF_MOBILE_DDR, 1.8V	DIFF_MOBILE_DDR	$0.9 - 0.125$	$0.9 + 0.125$	$0^{(5)}$	—
DIFF_HSTL, Class I, 1.2V	DIFF_HSTL_I_12	$0.6 - 0.125$	$0.6 + 0.125$	$0^{(5)}$	—
DIFF_HSTL, Class I & II, 1.5V	DIFF_HSTL_I, DIFF_HSTL_II	$0.75 - 0.125$	$0.75 + 0.125$	$0^{(5)}$	—
DIFF_HSTL, Class I & II, 1.8V	DIFF_HSTL_I_18, DIFF_HSTL_II_18	$0.9 - 0.125$	$0.9 + 0.125$	$0^{(5)}$	—
DIFF_HSUL, 1.2V	DIFF_HSUL_12	$0.6 - 0.125$	$0.6 + 0.125$	$0^{(5)}$	—
DIFF_SSTL135/ DIFF_SSTL135_R, 1.35V	DIFF_SSTL135, DIFF_SSTL135_R	$0.675 - 0.125$	$0.675 + 0.125$	$0^{(5)}$	—
DIFF_SSTL15/ DIFF_SSTL15_R, 1.5V	DIFF_SSTL15, DIFF_SSTL15_R	$0.75 - 0.125$	$0.75 + 0.125$	$0^{(5)}$	—
DIFF_SSTL18_I/ DIFF_SSTL18_II, 1.8V	DIFF_SSTL18_I, DIFF_SSTL18_II	$0.9 - 0.125$	$0.9 + 0.125$	$0^{(5)}$	—
LVDS_25, 2.5V	LVDS_25	$1.2 - 0.125$	$1.2 + 0.125$	$0^{(5)}$	—
BLVDS_25, 2.5V	BLVDS_25	$1.25 - 0.125$	$1.25 + 0.125$	$0^{(5)}$	—
MINI_LVDS_25, 2.5V	MINI_LVDS_25	$1.25 - 0.125$	$1.25 + 0.125$	$0^{(5)}$	—

Input/Output Delay Switching Characteristics

Table 25: Input/Output Delay Switching Characteristics

Symbol	Description	V _{CCINT} Operating Voltage and Speed Grade			Units
		1.0V		0.95V	
		-2	-1	-1L	
IDELAYCTRL					
T _{DLYCCO_RDY}	Reset to ready for IDELAYCTRL.	3.67	3.67	3.67	μs
F _{IDELAYCTRL_REF}	Attribute REFCLK frequency = 200.00. ⁽¹⁾	200.00	200.00	200.00	MHz
	Attribute REFCLK frequency = 300.00. ⁽¹⁾	300.00	300.00	300.00	MHz
	Attribute REFCLK frequency = 400.00. ⁽¹⁾	400.00	N/A	N/A	MHz
IDELAYCTRL_REF_PRECISION	REFCLK precision	±10	±10	±10	MHz
T _{IDELAYCTRL_RPW}	Minimum reset pulse width.	59.28	59.28	59.28	ns
IDELAY					
T _{IDELAYRESOLUTION}	IDELAY chain delay resolution.	1/(32 x 2 x F _{REF})			μs
T _{IDELAYPAT_JIT}	Pattern dependent period jitter in delay chain for clock pattern. ⁽²⁾	0	0	0	ps per tap
	Pattern dependent period jitter in delay chain for random data pattern (PRBS 23). ⁽³⁾	±5	±5	±5	ps per tap
	Pattern dependent period jitter in delay chain for random data pattern (PRBS 23). ⁽⁴⁾	±9	±9	±9	ps per tap
T _{IDELAY_CLK_MAX}	Maximum frequency of CLK input to IDELAY.	680.00	600.00	600.00	MHz
T _{IDCCK_CE} / T _{IDCKC_CE}	CE pin setup/hold with respect to C for IDELAY.	0.16/0.13	0.21/0.16	0.21/0.16	ns
T _{IDCCK_INC} /T _{IDCKC_INC}	INC pin setup/hold with respect to C for IDELAY.	0.14/0.18	0.16/0.22	0.16/0.22	ns
T _{IDCCK_RST} /T _{IDCKC_RST}	RST pin setup/hold with respect to C for IDELAY.	0.16/0.11	0.18/0.14	0.18/0.14	ns
T _{IDDO_IDATAIN}	Propagation delay through IDELAY.	Note 5	Note 5	Note 5	ps

Notes:

1. Average tap delay at 200 MHz = 78 ps, at 300 MHz = 52 ps, and at 400 MHz = 39 ps.
2. When HIGH_PERFORMANCE mode is set to TRUE or FALSE.
3. When HIGH_PERFORMANCE mode is set to TRUE.
4. When HIGH_PERFORMANCE mode is set to FALSE.
5. Delay depends on IDELAY tap setting. See the timing report for actual values.

Table 26: IO_FIFO Switching Characteristics

Symbol	Description	V _{CCINT} Operating Voltage and Speed Grade			Units
		1.0V		0.95V	
		-2	-1	-1L	
IO_FIFO Clock to Out Delays					
T _{OFFCKO_DO}	RDCLK to Q outputs.	0.60	0.68	0.68	ns
T _{CKO_FLAGS}	Clock to IO_FIFO flags.	0.61	0.77	0.77	ns
Setup/Hold					
T _{CCK_D} /T _{CKC_D}	D inputs to WRCLK.	0.51/0.02	0.58/0.02	0.58/0.02	ns
T _{IFFCCK_WREN} / T _{IFFCKC_WREN}	WREN to WRCLK.	0.47/−0.01	0.53/−0.01	0.53/−0.01	ns
T _{OFFCCK_RDEN} / T _{OFFCKC_RDEN}	RDEN to RDCLK.	0.58/0.02	0.66/0.02	0.66/0.02	ns
Minimum Pulse Width					
T _{PWH_IO_FIFO}	RESET, RDCLK, WRCLK.	2.15	2.15	2.15	ns
T _{PWL_IO_FIFO}	RESET, RDCLK, WRCLK.	2.15	2.15	2.15	ns
Maximum Frequency					
F _{MAX}	RDCLK and WRCLK.	200.00	200.00	200.00	MHz

Table 30: Block RAM and FIFO Switching Characteristics (Cont'd)

Symbol	Description	V _{CCINT} Operating Voltage and Speed Grade			Units
		1.0V		0.95V	
		-2	-1	-1L	
T _{RDCK_DI_ECC_FIFO} / T _{RCKD_DI_ECC_FIFO}	DIN inputs with FIFO ECC in standard mode. ⁽⁸⁾	1.15/0.59	1.32/0.64	1.32/0.64	ns, Min
T _{RCKC_INJECTBITERR} / T _{RCKC_INJECTBITERR}	Inject single/double bit error in ECC mode.	0.64/0.37	0.74/0.40	0.74/0.40	ns, Min
T _{RCKC_EN} /T _{RCKC_EN}	Block RAM enable (EN) input.	0.39/0.21	0.45/0.23	0.45/0.23	ns, Min
T _{RCKC_REGCE} / T _{RCKC_REGCE}	CE input of output register.	0.29/0.15	0.36/0.16	0.36/0.16	ns, Min
T _{RCKC_RSTREG} / T _{RCKC_RSTREG}	Synchronous RSTREG input.	0.32/0.07	0.35/0.07	0.35/0.07	ns, Min
T _{RCKC_RSTRAM} / T _{RCKC_RSTRAM}	Synchronous RSTRAM input.	0.34/0.43	0.36/0.46	0.36/0.46	ns, Min
T _{RCKC_WEA} /T _{RCKC_WEA}	Write enable (WE) input (block RAM only).	0.48/0.19	0.54/0.20	0.54/0.20	ns, Min
T _{RCKC_WREN} / T _{RCKC_WREN}	WREN FIFO inputs.	0.46/0.35	0.47/0.43	0.47/0.43	ns, Min
T _{RCKC_RDEN} / T _{RCKC_RDEN}	RDEN FIFO inputs.	0.43/0.35	0.43/0.43	0.43/0.43	ns, Min
Reset Delays					
T _{RCO_FLAGS}	Reset RST to FIFO flags/pointers. ⁽⁹⁾	0.98	1.10	1.10	ns, Max
T _{RREC_RST} /T _{RREM_RST}	FIFO reset recovery and removal timing. ⁽¹⁰⁾	2.07/–0.81	2.37/–0.81	2.37/–0.81	ns, Max
Maximum Frequency					
F _{MAX_BRAM_WF_NC}	Block RAM (write first and no change modes) when not in SDP RF mode.	460.83	388.20	388.20	MHz
F _{MAX_BRAM_RF_PERFORMANCE}	Block RAM (read first, performance mode) when in SDP RF mode but no address overlap between port A and port B.	460.83	388.20	388.20	MHz
F _{MAX_BRAM_RF_DELAYED_WRITE}	Block RAM (read first, delayed write mode) when in SDP RF mode and there is possibility of overlap between port A and port B addresses.	404.53	339.67	339.67	MHz
F _{MAX_CAS_WF_NC}	Block RAM cascade (write first, no change mode) when cascade but not in RF mode.	418.59	345.78	345.78	MHz
F _{MAX_CAS_RF_PERFORMANCE}	Block RAM cascade (read first, performance mode) when in cascade with RF mode and no possibility of address overlap/one port is disabled.	418.59	345.78	345.78	MHz

DSP48E1 Switching Characteristics

Table 31: DSP48E1 Switching Characteristics

Symbol	Description	V _{CCINT} Operating Voltage and Speed Grade			Units
		1.0V		0.95V	
		-2	-1	-1L	
Setup and Hold Times of Data/Control Pins to the Input Register Clock					
T _{DSPDCK_A_AREG} / T _{DSPCKD_A_AREG}	A input to A register CLK.	0.30/ 0.13	0.37/ 0.14	0.37/ 0.14	ns
T _{DSPDCK_B_BREG} / T _{DSPCKD_B_BREG}	B input to B register CLK.	0.38/ 0.16	0.45/ 0.18	0.45/ 0.18	ns
T _{DSPDCK_C_CREG} / T _{DSPCKD_C_CREG}	C input to C register CLK.	0.20/ 0.19	0.24/ 0.21	0.24/ 0.21	ns
T _{DSPDCK_D_DREG} / T _{DSPCKD_D_DREG}	D input to D register CLK.	0.32/ 0.27	0.42/ 0.27	0.42/ 0.27	ns
T _{DSPDCK_ACIN_AREG} / T _{DSPCKD_ACIN_AREG}	ACIN input to A register CLK.	0.27/ 0.13	0.32/ 0.14	0.32/ 0.14	ns
T _{DSPDCK_BCIN_BREG} / T _{DSPCKD_BCIN_BREG}	BCIN input to B register CLK.	0.29/ 0.16	0.36/ 0.18	0.36/ 0.18	ns
Setup and Hold Times of Data Pins to the Pipeline Register Clock					
T _{DSPDCK_{A, B}_MREG_MULT} / T _{DSPCKD_{A, B}_MREG_MULT}	{A, B} input to M register CLK using multiplier.	2.76/ −0.01	3.29/ −0.01	3.29/ −0.01	ns
T _{DSPDCK_{A, D}_ADREG} / T _{DSPCKD_{A, D}_ADREG}	{A, D} input to AD register CLK.	1.48/ −0.02	1.76/ −0.02	1.76/ −0.02	ns
Setup and Hold Times of Data/Control Pins to the Output Register Clock					
T _{DSPDCK_{A, B}_PREG_MULT} / T _{DSPCKD_{A, B}_PREG_MULT}	{A, B} input to P register CLK using multiplier.	4.60/ −0.28	5.48/ −0.28	5.48/ −0.28	ns
T _{DSPDCK_D_PREG_MULT} / T _{DSPCKD_D_PREG_MULT}	D input to P register CLK using multiplier.	4.50/ −0.73	5.35/ −0.73	5.35/ −0.73	ns
T _{DSPDCK_{A, B}_PREG} / T _{DSPCKD_{A, B}_PREG}	A or B input to P register CLK not using multiplier.	1.98/ −0.28	2.35/ −0.28	2.35/ −0.28	ns
T _{DSPDCK_C_PREG} / T _{DSPCKD_C_PREG}	C input to P register CLK not using multiplier.	1.76/ −0.26	2.10/ −0.26	2.10/ −0.26	ns
T _{DSPDCK_PCIN_PREG} / T _{DSPCKD_PCIN_PREG}	PCIN input to P register CLK.	1.51/ −0.15	1.80/ −0.15	1.80/ −0.15	ns
Setup and Hold Times of the CE Pins					
T _{DSPDCK_{CEA;CEB}_{AREG;BREG}} / T _{DSPCKD_{CEA;CEB}_{AREG;BREG}}	{CEA; CEB} input to {A; B} register CLK.	0.42/ 0.08	0.52/ 0.11	0.52/ 0.11	ns
T _{DSPDCK_CEC_CREG} / T _{DSPCKD_CEC_CREG}	CEC input to C register CLK.	0.34/ 0.11	0.42/ 0.13	0.42/ 0.13	ns
T _{DSPDCK_CED_DREG} / T _{DSPCKD_CED_DREG}	CED input to D register CLK.	0.43/ −0.03	0.52/ −0.03	0.52/ −0.03	ns

Table 31: DSP48E1 Switching Characteristics (Cont'd)

Symbol	Description	V _{CCINT} Operating Voltage and Speed Grade			Units
		1.0V		0.95V	
		-2	-1	-1L	
T _{DSPDCK_CEM_MREG} / T _{DSPCKD_CEM_MREG}	CEM input to M register CLK.	0.21/ 0.20	0.27/ 0.23	0.27/ 0.23	ns
T _{DSPDCK_CEP_PREG} / T _{DSPCKD_CEP_PREG}	CEP input to P register CLK.	0.43/ 0.01	0.53/ 0.01	0.53/ 0.01	ns
Setup and Hold Times of the RST Pins					
T _{DSPDCK_{RSTA; RSTB}_{AREG; BREG}}} / T _{DSPCKD_{RSTA; RSTB}_{AREG; BREG}}}	{RSTA, RSTB} input to {A, B} register CLK.	0.46/ 0.13	0.55/ 0.15	0.55/ 0.15	ns
T _{DSPDCK_RSTC_CREG} / T _{DSPCKD_RSTC_CREG}	RSTC input to C register CLK.	0.08/ 0.11	0.09/ 0.12	0.09/ 0.12	ns
T _{DSPDCK_RSTD_DREG} / T _{DSPCKD_RSTD_DREG}	RSTD input to D register CLK	0.50/ 0.08	0.59/ 0.09	0.59/ 0.09	ns
T _{DSPDCK_RSTM_MREG} / T _{DSPCKD_RSTM_MREG}	RSTM input to M register CLK	0.23/ 0.24	0.27/ 0.28	0.27/ 0.28	ns
T _{DSPDCK_RSTP_PREG} / T _{DSPCKD_RSTP_PREG}	RSTP input to P register CLK	0.30/ 0.01	0.35/ 0.01	0.35/ 0.01	ns
Combinatorial Delays from Input Pins to Output Pins					
T _{DSPDO_A_CARRYOUT_MULT}	A input to CARRYOUT output using multiplier.	4.35	5.18	5.18	ns
T _{DSPDO_D_P_MULT}	D input to P output using multiplier.	4.26	5.07	5.07	ns
T _{DSPDO_B_P}	B input to P output not using multiplier.	1.75	2.08	2.08	ns
T _{DSPDO_C_P}	C input to P output.	1.53	1.82	1.82	ns
Combinatorial Delays from Input Pins to Cascading Output Pins					
T _{DSPDO_{A; B}_{ACOUT; BCOUT}}}	{A, B} input to {ACOUT, BCOUT} output.	0.63	0.74	0.74	ns
T _{DSPDO_{A, B}_CARRYCASCOUT_MULT}}	{A, B} input to CARRYCASCOUT output using multiplier.	4.65	5.54	5.54	ns
T _{DSPDO_D_CARRYCASCOUT_MULT}	D input to CARRYCASCOUT output using multiplier.	4.54	5.40	5.40	ns
T _{DSPDO_{A, B}_CARRYCASCOUT}	{A, B} input to CARRYCASCOUT output not using multiplier.	2.03	2.41	2.41	ns
T _{DSPDO_C_CARRYCASCOUT}	C input to CARRYCASCOUT output.	1.81	2.15	2.15	ns
Combinatorial Delays from Cascading Input Pins to All Output Pins					
T _{DSPDO_ACIN_P_MULT}	ACIN input to P output using multiplier.	4.19	5.00	5.00	ns
T _{DSPDO_ACIN_P}	ACIN input to P output not using multiplier.	1.57	1.88	1.88	ns
T _{DSPDO_ACIN_ACOUT}	ACIN input to ACOUT output.	0.44	0.53	0.53	ns
T _{DSPDO_ACIN_CARRYCASCOUT_MULT}	ACIN input to CARRYCASCOUT output using multiplier.	4.47	5.33	5.33	ns
T _{DSPDO_ACIN_CARRYCASCOUT}	ACIN input to CARRYCASCOUT output not using multiplier.	1.85	2.21	2.21	ns
T _{DSPDO_PCIN_P}	PCIN input to P output.	1.28	1.52	1.52	ns

Clock Buffers and Networks

Table 32: Global Clock Switching Characteristics (Including BUFGCTRL)

Symbol	Description	V _{CCINT} Operating Voltage and Speed Grade			Units
		1.0V		0.95V	
		-2	-1	-1L	
T _{BCCCK_CE} /T _{BCCCK_CE} ⁽¹⁾	CE pins setup/hold.	0.13/0.40	0.16/0.41	0.16/0.41	ns
T _{BCCCK_S} /T _{BCCCK_S} ⁽¹⁾	S pins setup/hold.	0.13/0.40	0.16/0.41	0.16/0.41	ns
T _{BCKO_O} ⁽²⁾	BUFGCTRL delay from I0/I1 to O.	0.09	0.10	0.10	ns
Maximum Frequency					
F _{MAX_BUFG}	Global clock tree (BUFG).	628.00	464.00	464.00	MHz

Notes:

1. T_{BCCCK_CE} and T_{BCCCK_CE} must be satisfied to assure glitch-free operation of the global clock when switching between clocks. These parameters do not apply to the BUFGMUX primitive that assures glitch-free operation. The other global clock setup and hold times are optional; only needing to be satisfied if device operation requires simulation matches on a cycle-for-cycle basis when switching between clocks.
2. T_{BCKO_O} (BUFG delay from I0 to O) values are the same as T_{BCKO_O} values.

Table 33: Input/Output Clock Switching Characteristics (BUFIO)

Symbol	Description	V _{CCINT} Operating Voltage and Speed Grade			Units
		1.0V		0.95V	
		-2	-1	-1L	
T _{BIOCKO_O}	Clock to out delay from I to O.	1.26	1.54	1.54	ns
Maximum Frequency					
F _{MAX_BUFIO}	I/O clock tree (BUFIO).	680.00	600.00	600.00	MHz

Table 34: Regional Clock Buffer Switching Characteristics (BUFR)

Symbol	Description	V _{CCINT} Operating Voltage and Speed Grade			Units
		1.0V		0.95V	
		-2	-1	-1L	
T _{BRCKO_O}	Clock to out delay from I to O.	0.76	0.99	0.99	ns
T _{BRCKO_O_BYP}	Clock to out delay from I to O with Divide Bypass attribute set.	0.39	0.52	0.52	ns
T _{BRDO_O}	Propagation delay from CLR to O.	0.85	1.09	1.09	ns
Maximum Frequency					
F _{MAX_BUFR} ⁽¹⁾	Regional clock tree (BUFR).	375.00	315.00	315.00	MHz

Notes:

1. The maximum input frequency to the BUFR is the BUFIO F_{MAX} frequency.

Device Pin-to-Pin Output Parameter Guidelines

Table 39: Clock-Capable Clock Input to Output Delay Without MMCM/PLL (Near Clock Region)⁽¹⁾

Symbol	Description	Device	V _{CCINT} Operating Voltage and Speed Grade			Units
			1.0V		0.95V	
			-2	-1	-1L	
SSTL15 Clock-Capable Clock Input to Output Delay using Output Flip-Flop, Fast Slew Rate, <i>without</i> MMCM/PLL.						
T _{ICKOF}	Clock-capable clock input and OUTFF at pins/banks closest to the BUFGs <i>without</i> MMCM/PLL (near clock region). ⁽²⁾	XC7S6	5.55	6.50	6.50	ns
		XC7S15	5.55	6.50	6.50	ns
		XC7S25	5.55	6.44	6.44	ns
		XC7S50	5.71	6.62	6.62	ns
		XC7S75	5.73	6.71	6.71	ns
		XC7S100	5.73	6.71	6.71	ns
		XA7S6	5.55	6.50	N/A	ns
		XA7S15	5.55	6.50	N/A	ns
		XA7S25	5.55	6.44	N/A	ns
		XA7S50	5.71	6.62	N/A	ns
		XA7S75	5.73	6.71	N/A	ns
		XA7S100	5.73	6.71	N/A	ns

Notes:

1. This table lists representative values where one global clock input drives one vertical clock line in each accessible column, and where all accessible IOB and CLB flip-flops are clocked by the global clock net.
2. Refer to the *Die Level Bank Numbering Overview* section of the *7 Series FPGA Packaging and Pinout Specification* (UG475) [Ref 4].

Table 48: Sample Window

Symbol	Description	V _{CCINT} Operating Voltage and Speed Grade			Units
		1.0V		0.95V	
		-2	-1	-1L	
T _{SAMP}	Sampling error at receiver pins. ⁽¹⁾	0.64	0.70	0.70	ns
T _{SAMP_BUFIO}	Sampling error at receiver pins using BUFIO. ⁽²⁾	0.40	0.46	0.46	ns

Notes:

1. This parameter indicates the total sampling error of the Spartan-7 FPGAs DDR input registers, measured across voltage, temperature, and process. The characterization methodology uses the MMCM to capture the DDR input registers' edges of operation. These measurements include:
 - CLK0 MMCM jitter
 - MMCM accuracy (phase offset)
 - MMCM phase shift resolution
These measurements do not include package or clock tree skew.
2. This parameter indicates the total sampling error of the Spartan-7 FPGAs DDR input registers, measured across voltage, temperature, and process. The characterization methodology uses the BUFIO clock network and IDELAY to capture the DDR input registers' edges of operation. These measurements do not include package or clock tree skew.

Additional Package Parameter Guidelines

The parameters in this section provide the necessary values for calculating timing budgets for Spartan-7 FPGA clock transmitter and receiver data-valid windows.

Table 49: Package Skew⁽¹⁾

Symbol	Description	Device	Package	Value	Units
$T_{PKGSKEW}$	Package skew. ⁽²⁾	XC7S6	CPGA196	44	ps
			CSGA225	83	ps
			FTGB196	65	ps
		XC7S15	CPGA196	44	ps
			CSGA225	83	ps
			FTGB196	65	ps
		XC7S25	CSGA225	93	ps
			CSGA324	62	ps
			FTGB196	83	ps
		XC7S50	CSGA324	80	ps
			FGGA484	110	ps
			FTGB196	103	ps
		XC7S75	FGGA484	117	ps
			FGGA676	110	ps
		XC7S100	FGGA484	117	ps
			FGGA676	110	ps
		XA7S6	CPGA196	44	ps
			CSGA225	83	ps
			FTGB196	65	ps
		XA7S15	CPGA196	44	ps
			CSGA225	83	ps
			FTGB196	65	ps
		XA7S25	CSGA225	93	ps
			CSGA324	62	ps
			FTGB196	83	ps
		XA7S50	CSGA324	80	ps
			FGGA484	110	ps
			FTGB196	103	ps
		XA7S75	FGGA484	117	ps
			FGGA676	110	ps
		XC7S100	FGGA484	117	ps
			FGGA676	110	ps

Notes:

- Package delay information is available for these device/package combinations. This information can be used to deskew the package.
- These values represent the worst-case skew between any two SelectIO resources in the package: shortest delay to longest delay from die pad to ball.

XADC Specifications

The 7 Series FPGAs Overview (DS180) [Ref 1] and XA Spartan-7 Automotive FPGA Data Sheet: Overview (DS171) [Ref 2] list the devices that contain a 7 series XADC dual 12-Bit 1 MSPS analog-to-digital converter.

Table 50: XADC Specifications

Parameter	Symbol	Comments/Conditions	Min	Typ	Max	Units
$V_{CCADC} = 1.8V \pm 5\%$, $V_{REFP} = 1.25V$, $V_{REFN} = 0V$, $ADCCLK = 26\text{ MHz}$, $-55^{\circ}\text{C} \leq T_j \leq 125^{\circ}\text{C}$. Typical values at $T_j = +40^{\circ}\text{C}$.						
ADC Accuracy⁽¹⁾						
Resolution			12	–	–	Bits
Integral nonlinearity ⁽²⁾	INL	$-40^{\circ}\text{C} \leq T_j \leq 100^{\circ}\text{C}$	–	–	± 2	LSBs
		$-55^{\circ}\text{C} \leq T_j < -40^{\circ}\text{C}$; $100^{\circ}\text{C} < T_j \leq 125^{\circ}\text{C}$	–	–	± 3	LSBs
Differential nonlinearity	DNL	No missing codes, guaranteed monotonic.	–	–	± 1	LSBs
Offset error	Unipolar	$-40^{\circ}\text{C} \leq T_j \leq 100^{\circ}\text{C}$	–	–	± 8	LSBs
		$-55^{\circ}\text{C} \leq T_j < -40^{\circ}\text{C}$; $100^{\circ}\text{C} < T_j \leq 125^{\circ}\text{C}$	–	–	± 12	LSBs
	Bipolar	$-55^{\circ}\text{C} \leq T_j \leq 125^{\circ}\text{C}$	–	–	± 4	LSBs
Gain error			–	–	± 0.5	%
Offset matching			–	–	4	LSBs
Gain matching			–	–	0.3	%
Sample rate			–	–	1	MS/s
Signal to noise ratio ⁽²⁾	SNR	$F_{SAMPLE} = 500\text{ KS/s}$, $F_{IN} = 20\text{ kHz}$	60	–	–	dB
RMS code noise		External 1.25V reference.	–	–	2	LSBs
		On-chip reference.	–	3	–	LSBs
Total harmonic distortion ⁽²⁾	THD	$F_{SAMPLE} = 500\text{ KS/s}$, $F_{IN} = 20\text{ kHz}$	70	–	–	dB
Analog Inputs⁽³⁾						
ADC input ranges		Unipolar operation.	0	–	1	V
		Bipolar operation.	–0.5	–	+0.5	V
		Unipolar common mode range (FS input).	0	–	+0.5	V
		Bipolar common mode range (FS input).	+0.5	–	+0.6	V
Maximum external channel input ranges		Adjacent analog channels set within these ranges should not corrupt measurements on adjacent channels.	–0.1	–	V_{CCADC}	V
Full-resolution bandwidth	FRBW	Auxiliary channel full resolution bandwidth.	250	–	–	kHz
On-chip Sensors						
Temperature sensor error		$-40^{\circ}\text{C} \leq T_j \leq 100^{\circ}\text{C}$	–	–	± 4	$^{\circ}\text{C}$
		$-55^{\circ}\text{C} \leq T_j < -40^{\circ}\text{C}$; $100^{\circ}\text{C} < T_j \leq 125^{\circ}\text{C}$	–	–	± 6	$^{\circ}\text{C}$
Supply sensor error		$-40^{\circ}\text{C} \leq T_j \leq 100^{\circ}\text{C}$	–	–	± 1	%
		$-55^{\circ}\text{C} \leq T_j < -40^{\circ}\text{C}$; $100^{\circ}\text{C} < T_j \leq 125^{\circ}\text{C}$	–	–	± 2	%

Table 51: Configuration Switching Characteristics (Cont'd)

Symbol	Description	V _{CCINT} Operating Voltage and Speed Grade			Units
		1.0V		0.95V	
		-2	-1	-1L	
T _{SMCSCCK} / T _{SMCCKCS}	CSI_B setup/hold.	4.00/0.00	4.00/0.00	4.00/0.00	ns, Min
T _{SMWCCK} / T _{SMCCKW}	RDWR_B setup/hold.	10.00/0.00	10.00/0.00	10.00/0.00	ns, Min
T _{SMCKCSO}	CSO_B clock to out (330 Ω pull-up resistor required).	7.00	7.00	7.00	ns, Max
T _{SMCO}	D[31:00] clock to out in readback.	8.00	8.00	8.00	ns, Max
F _{RBCK}	Readback frequency.	100.00	100.00	100.00	MHz, Max
Boundary-Scan Port Timing Specifications					
T _{TAPTCK} / T _{TCKTAP}	TMS and TDI setup/hold.	3.00/2.00	3.00/2.00	3.00/2.00	ns, Min
T _{TCKTDO}	TCK falling edge to TDO output.	7.00	7.00	7.00	ns, Max
F _{TCK}	TCK frequency.	66.00	66.00	66.00	MHz, Max
SPI Flash Master Mode Programming Switching					
T _{SPIDCC} / T _{SPICCD}	D[03:00] setup/hold.	3.00/0.00	3.00/0.00	3.00/0.00	ns, Min
T _{SPICCM}	MOSI clock to out.	8.00	8.00	8.00	ns, Max
T _{SPICFC}	FCS_B clock to out.	8.00	8.00	8.00	ns, Max
STARTUPE2 Ports					
T _{USRCCLKO}	STARTUPE2 USRCCLKO input to CCLK output.	0.50/6.70	0.50/7.50	0.50/7.50	ns, Min/Max
F _{CFGMCLK}	STARTUPE2 CFGMCLK output frequency.	65.00	65.00	65.00	MHz, Typ
F _{CFGMCLKTOL}	STARTUPE2 CFGMCLK output frequency tolerance.	± 50	± 50	± 50	%, Max
Device DNA Access Port					
F _{DNACK}	DNA access port (DNA_PORT).	100.00	100.00	100.00	MHz, Max

Notes:

- To support longer delays in configuration, use the design solutions described in the *7 Series FPGA Configuration User Guide* (UG470) [Ref 10].
- See the *7 Series FPGAs Overview* (DS180) [Ref 1] and *XA Spartan-7 Automotive FPGA Data Sheet: Overview* (DS171) [Ref 2] for a list of devices that support bitstream encryption.

eFUSE Programming Conditions

Table 52 lists the programming conditions specifically for eFUSE. For more information, see the *7 Series FPGA Configuration User Guide* (UG470) [Ref 10].

Table 52: eFUSE Programming Conditions⁽¹⁾

Symbol	Description	Min	Typ	Max	Units
I_{FS}	V_{CCAUX} supply current	–	–	115	mA
T_j	Temperature range	15	–	125	°C

Notes:

1. The FPGA must not be configured during eFUSE programming.

References

1. *7 Series FPGAs Overview* (DS180)
2. *XA Spartan-7 Automotive FPGA Data Sheet: Overview* (DS171)
3. *7 Series FPGAs SelectIO Resources User Guide* (UG471)
4. *7 Series FPGA Packaging and Pinout Specification* (UG475)
5. *7 Series FPGAs PCB Design Guide* (UG483)
6. *Xilinx Power Estimator* spreadsheet tool (XPE)
7. *Zynq-7000 AP SoC and 7 Series FPGAs Memory Interface Solutions User Guide* (UG586)
8. See the [Clocking Wizard](#) in Vivado software.
9. *7 Series FPGAs and Zynq-7000 AP SoC XADC Dual 12-Bit 1 MSPS Analog-to-Digital Converter User Guide* (UG480)
10. *7 Series FPGA Configuration User Guide* (UG470)